



PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant :	Stephen P. Vernon et al.	Docket No. :	IL-11011
Serial No. :	10 676 876	Art Unit :	
Filed :	September 30, 2003	Examiner	
For :	Direct-Patterned Optical Waveguides on Amorphous Silicon Films		

Commissioner for Patents  
Alexandria, VA

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Docket No. IL-11011

Customer No: 24981

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Silicon Films

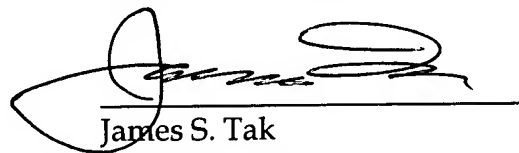
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Commissioner for Patents  
Alexandria, VA 22313-1450

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Forwarded herewith is an Information Disclosure Statement, Form-1449, in  
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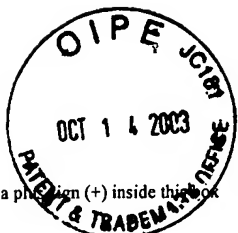
Respectfully submitted,



James S. Tak  
Agent for Applicants  
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Dated: 10-7-03

Enclosure:  
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10676 876

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PTO/SB/08A (08-00)

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		Application Number	
		Filing Date	
		First Named Inventor	
		Group Art Unit	
Examiner Name			
Attorney Docket Number		IL-11011	
Sheet	1	of	2

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			
		5,841,931		Foresi et al	Nov. 24, 1998	
		5,354,709		Joseph P. Lorenzo et al	Oct. 11, 1994	
		5,946,562		Yue Kuo	Aug. 31, 1999	
		6204099	B1	Kusumoto et al	March 20, 2001	

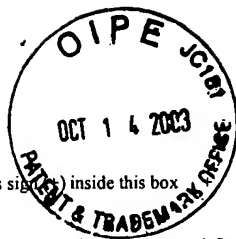
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Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				
		EP	0567051	B1	Kazuo, Eda	04/20/1993		

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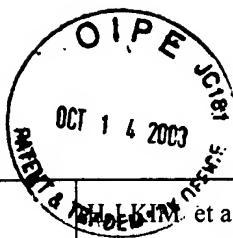
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Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (use as many sheets as necessary)		<b>Complete if Known</b>	
		Application Number	
		Filing Date 9/30/2003	
		First Named Inventor Stephen P. Vernon	
		Group Art Unit	
Examiner Name			
Sheet 2	IL- 2	Attorney Docket Number IL-11011	
<b>OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS</b>			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	
		KJARTAN FAERCH et al	Symmetrical Waveguide Devices Fabricated by Direct UV Writing IEEE Photonics Technology Letters., Vol. 14, No. 2 February 2002
		C.M. FORTMANN et al	Hot-wire deposition of photonic-grade amorphous silicon Thin Solid Films 395 (2001) 142-146
		GIUSEPPE COCORULLO et al	Amorphous Silicon-Based Guided-Wave Passive and Active Devices for Silicon Integrated Optoelectronics IEEE Journal of Selected Topics in Quantum Electronics, Vol. 4, No. 6, Nov/Dec 1998
		MICHAEL O. THOMPSON et al	Melting Temperature and Explosive Crystallization of Amorphous Silicon during Pulsed Laser Irradiation 1984 The American Physical Society Physical Review Letters Vol. 52, Number 26 June 25, 1984 pages 2360-2364
		OSAMU HANAIZUMI et al	Propagation of light beams along line defects formed in a-Si/SiO <sub>2</sub> 1999 American Institute of Physics Applied Physics Letters Volume 74, Number 6 pages 777-779
		S.R. STIFFLER et al	Supercooling and Nucleation of Silicon after Laser Melting 1988 The American Physical Society Physical Review Letters Vol. 60, Number 24, June 1988 pages 2523



		et al	New Excimer-laser-crystallization method for producing large-grained and grain boundary-location-controlled Si films for thin film transistors	Appl Phys. Lett 68 (11) March 11, 1996 Pages 1513-1515
		MINGHONG LEE et al	Relationship between fluence gradient and lateral grain growth in spatially controlled excimer laser crystallization of amorphous silicon films	Journal of Applied Physics Vol. 88 Number 9 November 1 2000
		HIROKI TAKAHASHI et al	Influence of Ar impurities on optical refractive index of sputter deposited a-Si films	Journal of Materials Research Vol 12, No. 7 July 1997
		M.H.BRODSKY et al	Structural,Optical, and Electrical Properties of Amorphous Silicon Films	Physical Review B Volume 1, Number 6 March 15, 1970
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